

Near-vertical plasma-free HCl gas etching on (011) β -Ga₂O₃

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This supplementary material presents magnified scanning electron microscopy (SEM) images of the right half of the etched trenches under the radial line windows, as shown in Figs. S1–S6. The magnified images of the left half are not included as the trenches in the same directions can be found in the right half.

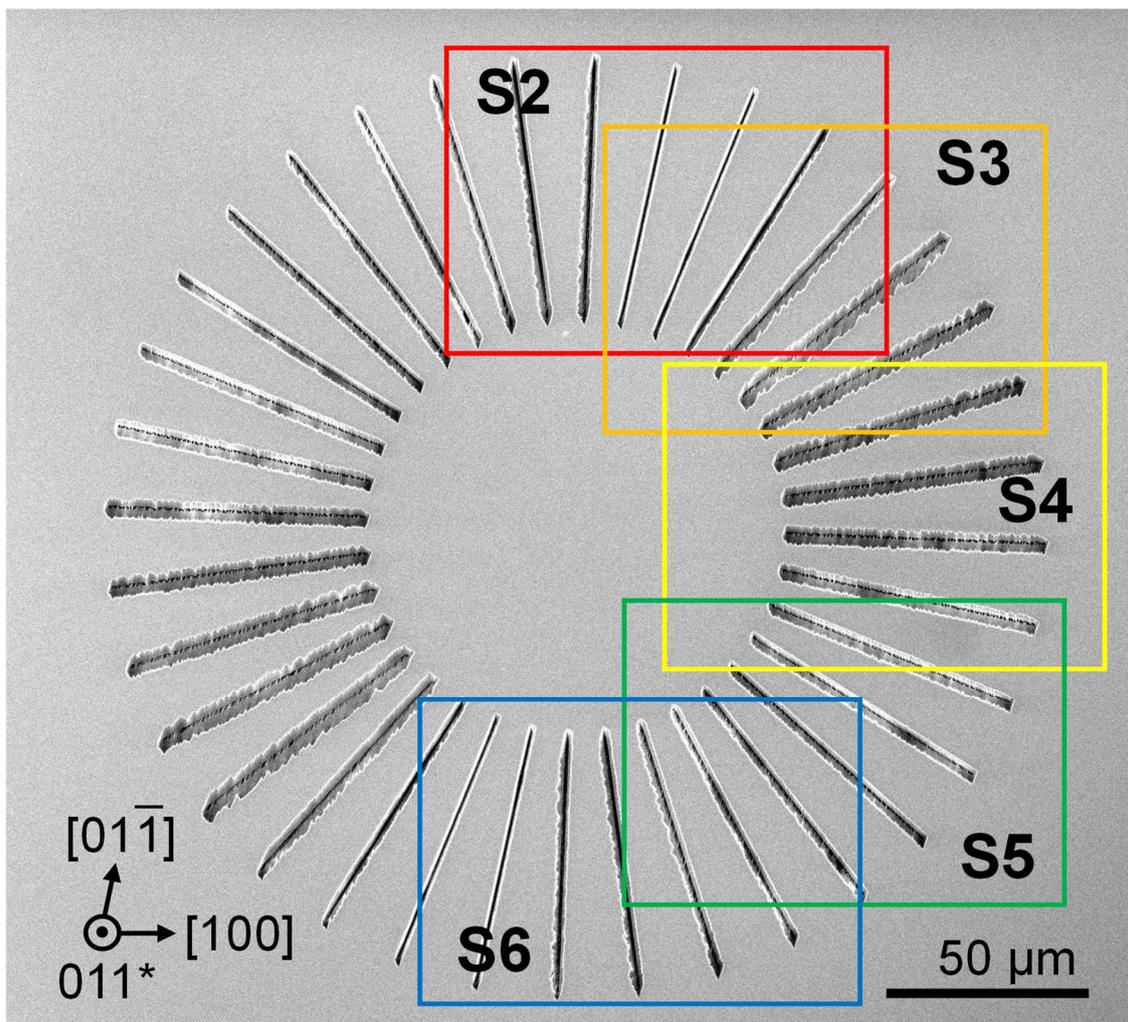


Figure S1. Plain-view SEM image of etched trenches under radial-line windows on (011) β -Ga₂O₃. The colored frames correspond to the areas of the magnified images of Figs. S2–S6. This image, with the exception of the frames, is same as Fig. 1(a) in the original paper.

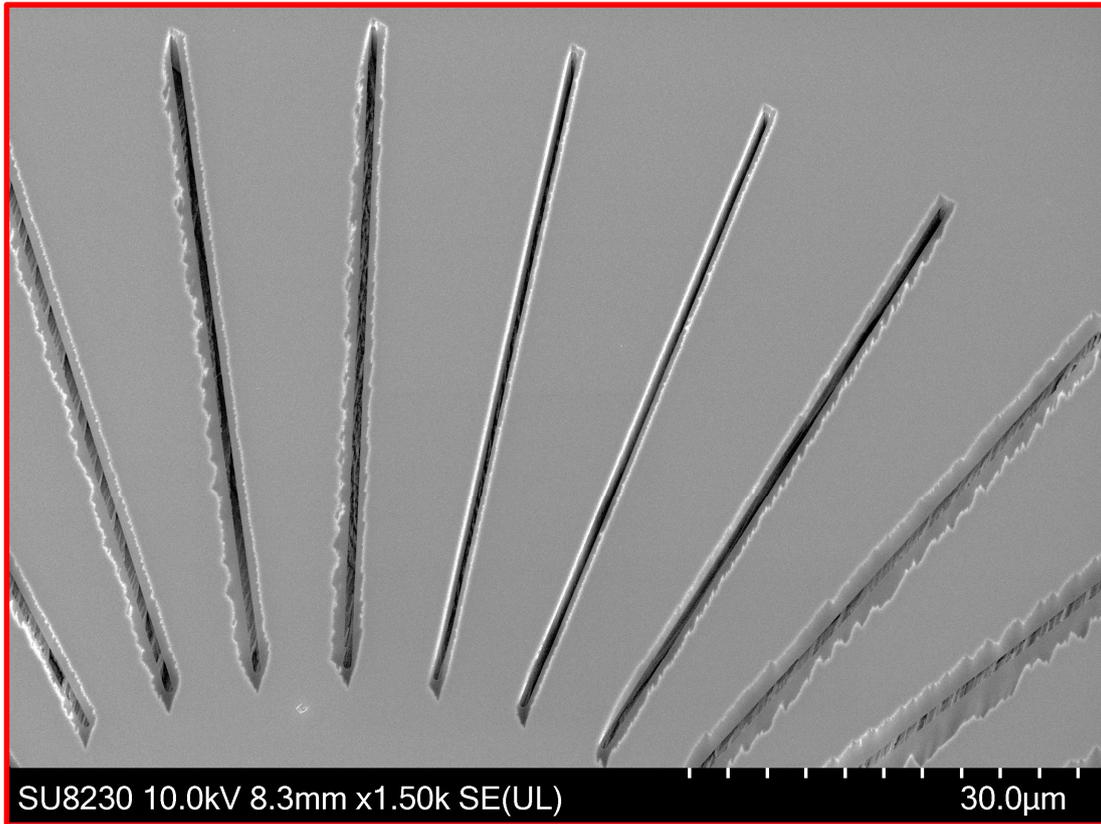


Figure S2. Plain-view SEM image of a part of the etched trenches under radial-line windows on (011) β -Ga₂O₃. For further details regarding the image area, refer to Fig. S1.

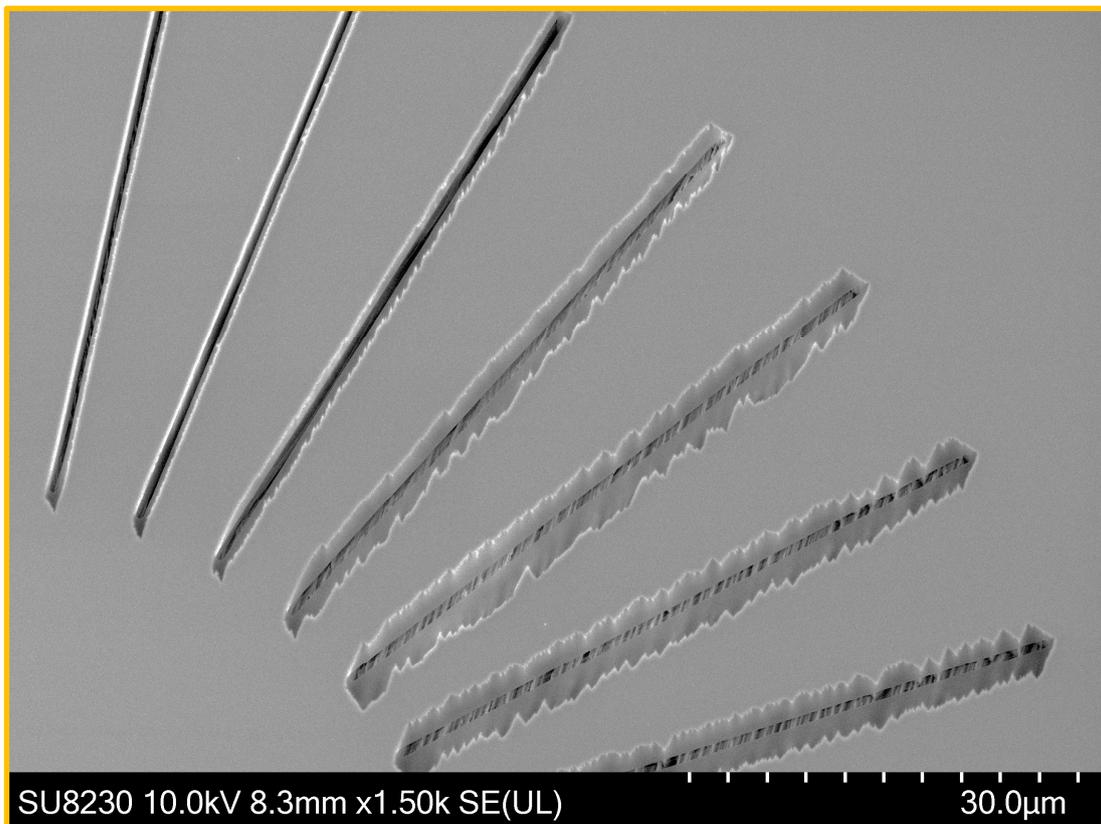


Figure S3. Plain-view SEM image of a part of the etched trenches under radial-line windows on (011) β -Ga₂O₃. For further details regarding the image area, refer to Fig. S1.

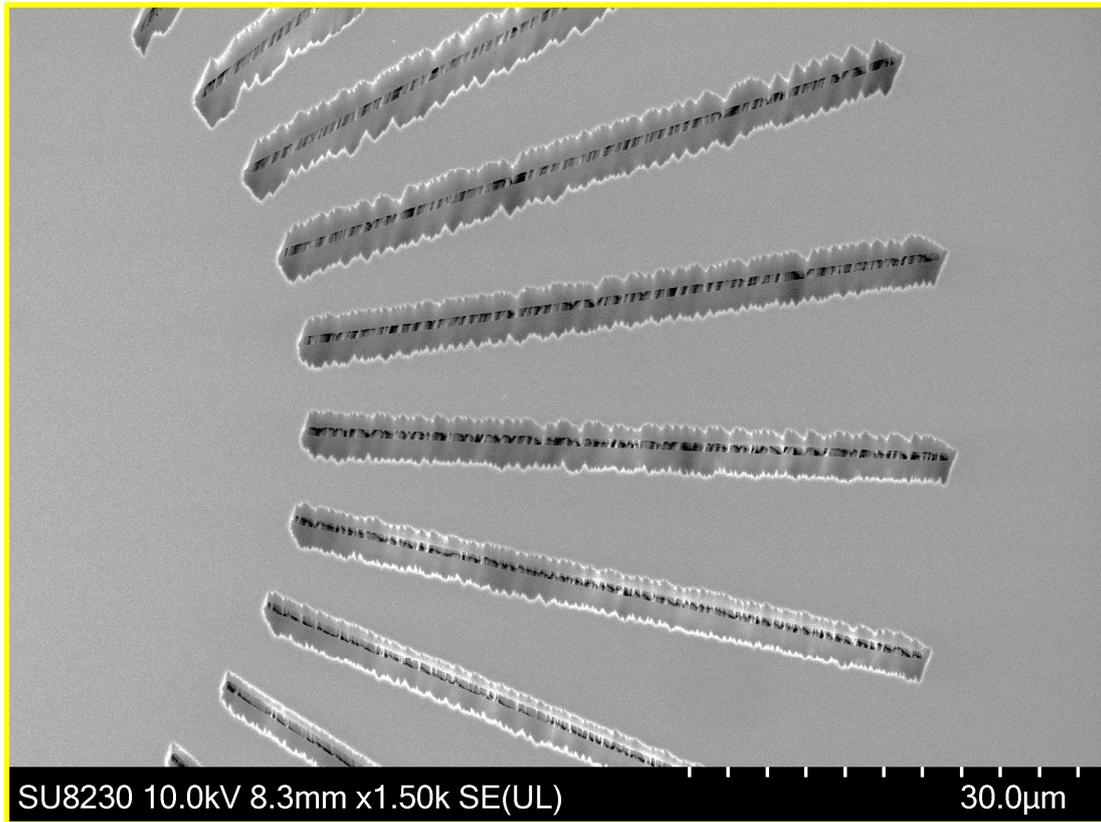


Figure S4. Plain-view SEM image of a part of the etched trenches under radial-line windows on (011) β -Ga₂O₃. For further details regarding the image area, refer to Fig. S1.

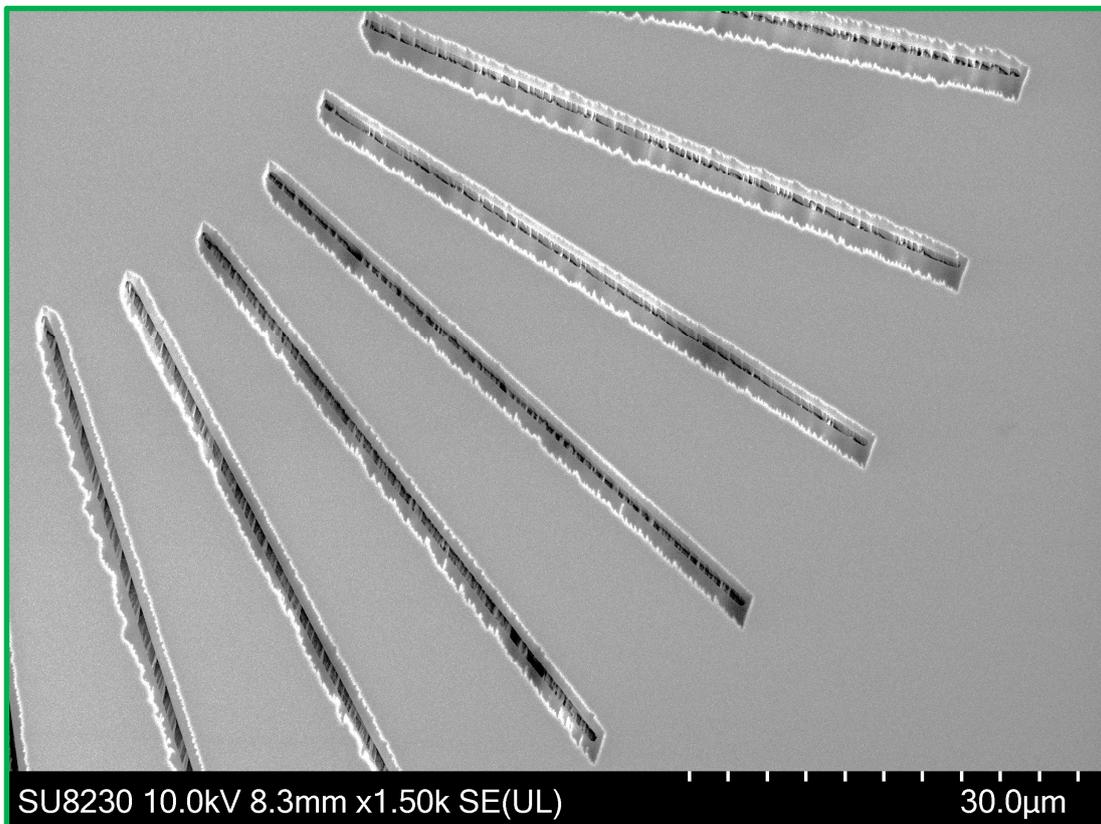


Figure S5. Plain-view SEM image of a part of the etched trenches under radial-line windows on (011) β -Ga₂O₃. For further details regarding the image area, refer to Fig. S1.

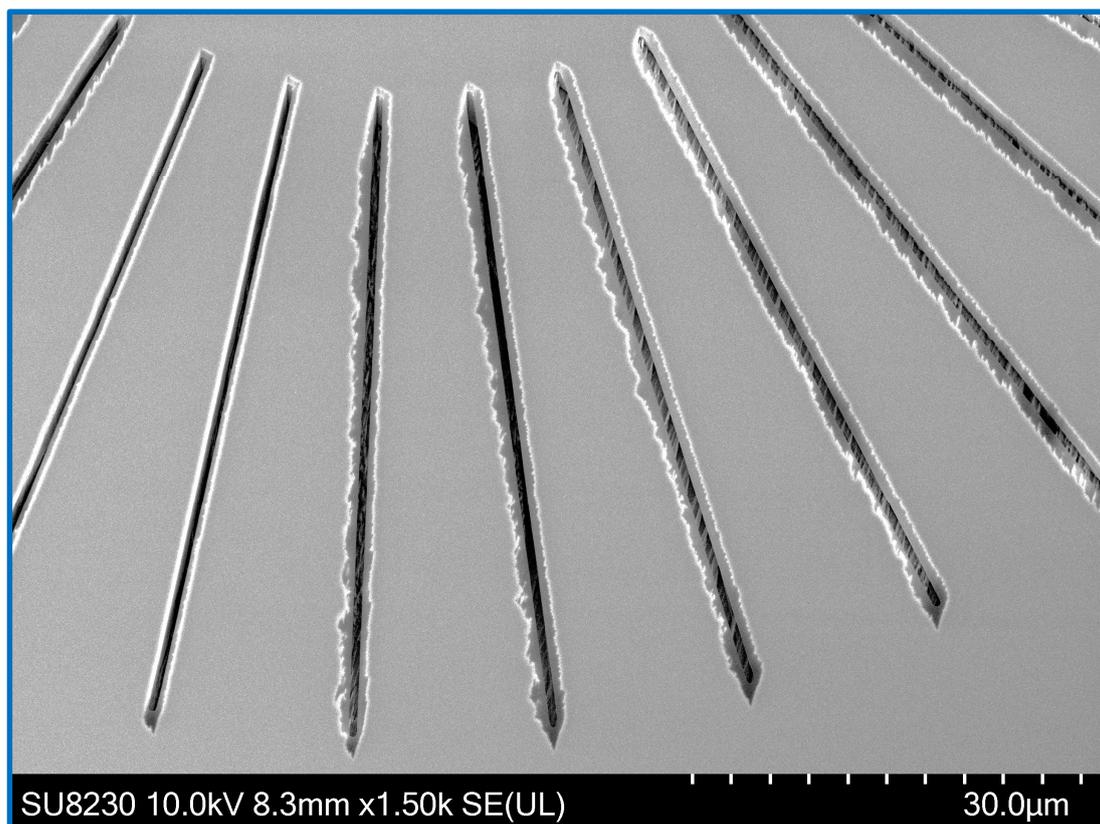


Figure S6. Plain-view SEM image of a part of the etched trenches under radial-line windows on (011) β -Ga₂O₃. For further details regarding the image area, refer to Fig. S1.